L Number	Hits	Search Text	DB	Time stamp
3	29	(US-6144093-$ or US-5821611-$ or US-4935803-$ or US-6566164-$ or US-6528880-$ or US-6521982-$ or US-6465276-$ or US-6459147-$ or US-6229196-$ or US-6396127-$ or US-6319755-$ or US-6307755-$ or US-6256200-$ or US-6255672-$ or US-5841197-$ or US-6249041-$ or US-6249136-$ or US-5814884-$ or US-6040626-$ or US-5929523-$ or US-4989058-$ or US-4199774-$ or US-5637922-$ or US-5105536-$ or US-6421262-$ or US-6282107-$).did. or (US-20010000631-$ or US-20030075796-$ or US-20020093094-$).did.	USPAT; US-PGPUB	2004/05/19 10:06
4	1	6282107.URPN.	USPAT	2004/05/19 10:00
5	12	("4975821" | "5126931" | "5331533" | "5374857" | "5434768" | "5734563" | "5774350" | "5805434" | "5812383" | "5814884" | "5886383" | "5973939").PN.	USPAT	2004/05/19 10:01
6	9	4989058.URPN.	USPAT	2004/05/19 10:04
7	11	("3788904" | "4199774" | "4250519" | "4270137" | "4300152" | "4300250" | "4358782" | "4513309" | "4633282" | "4639761" | "4694313").PN.	USPAT	2004/05/19 10:04
8	3217	soi and mosfet	USPAT; US-PGPUB	2004/05/19 10:06
9	0	vaiable with threshold with voltage with complementary with mosfet	USPAT; US-PGPUB; EPO; JPO	2004/05/19 10:07
10	91	threshold with voltage with complementary with mosfet	USPAT; US-PGPUB; EPO; JPO	2004/05/19 10:28
11	1532	"91" and soi	USPAT; US-PGPUB; EPO; JPO	2004/05/19 10:08
12	10	(threshold with voltage with complementary with mosfet) and soi	USPAT; US-PGPUB; EPO; JPO	2004/05/19 10:16
13	81	(threshold with voltage with complementary with mosfet) not ((threshold with voltage with complementary with mosfet) and soi)	USPAT; US-PGPUB; EPO; JPO	2004/05/19 10:16
14	0	((threshold with voltage with complementary with mosfet) not ((threshold with voltage with complementary with mosfet) and soi)) and (adjusted near1 bias)	USPAT; US-PGPUB; EPO; JPO	2004/05/19 10:17
15	45	((threshold with voltage with complementary with mosfet) not ((threshold with voltage with complementary with mosfet) and soi)) and bias	USPAT; US-PGPUB; EPO; JPO	2004/05/19 10:31
16	5434	threshold with voltage with mosfet	USPAT; US-PGPUB; EPO; JPO	2004/05/19 10:28
17	95011	threshold near3 voltage near3mosfet	USPAT; US-PGPUB; EPO; JPO	2004/05/19 10:29
18	3584	threshold near3 voltage near3 mosfet	USPAT; US-PGPUB; EPO; JPO	2004/05/19 10:29
19	582	(threshold near3 voltage near3 mosfet) and (soi (silicon near1 insulation))	USPAT; US-PGPUB; EPO; JPO	2004/05/19 10:30
20	78	((threshold near3 voltage near3 mosfet) and (soi (silicon near1 insulation))) and (second near1 mosfet)	USPAT; US-PGPUB; EPO; JPO	2004/05/19 10:31

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21	78	(((threshold near3 voltage near3 mosfet) and (soi (silicon near1 insulation))) and (second near1 mosfet)) not (((threshold with voltage with complementary with mosfet) not ((threshold with voltage with complementary with mosfet) and soi)) and bias)	USPAT; US-PGPUB; EPO; JPO	2004/05/19 10:31
22	42	(((threshold near3 voltage near3 mosfet) and (soi (silicon near1 insulation))) and (second near1 mosfet)) and bias	USPAT; US-PGPUB; EPO; JPO	2004/05/19 10:32
23	26	((((threshold near3 voltage near3 mosfet) and (soi (silicon near1 insulation))) and (second near1 mosfet)) and bias) and (gate adj electrode)	USPAT; US-PGPUB; EPO; JPO	2004/05/19 10:32
24	17	5488243.URPN.	USPAT	2004/05/19 10:35
25	1707	(threshold near3 voltage near3 mosfet) and bias	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/19 10:45
26	36	((threshold near3 voltage near3 mosfet) and bias) and (partial$3 near deplet$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/19 10:46
27	27	(((threshold near3 voltage near3 mosfet) and bias) and (partial$3 near deplet$3)) not (((((threshold near3 voltage near3 mosfet) and (soi (silicon near1 insulation))) and (second near1 mosfet)) and bias)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/19 10:58
28	0	6603175.URPN.	USPAT	2004/05/19 10:47
29	3	("5818781" | "6087893" | "6160292" | "2001/0045602").PN.	USPAT	2004/05/19 10:47
30	51	partially near3 depleted near3 SOI near3 MOSFET	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/19 14:21
31	43	(partially near3 depleted near3 SOI near3 MOSFET) and (threshold near2 voltage)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/19 13:16
32	8	6222234.URPN.	USPAT	2004/05/19 13:10
33	2	("5479033" | "5827755").PN.	USPAT	2004/05/19 13:11
35	0	6222234.pn. and (bias near electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/19 13:16
34	1	6222234.pn. and bias	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/19 14:59
36	2	"6461907"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/19 13:25
37	0	6461907.URPN.	USPAT	2004/05/19 13:26
38	6	("5081058" | "5145802" | "5479033" | "5650339" | "5728609" | "5827755").PN.	USPAT	2004/05/19 13:26
39	29	5479033.URPN.	USPAT	2004/05/19 13:28
40	1	6222234.pn. and ("n-channel" (n adj channel))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/19 14:20
41	0	6222234.pn. and ("p-channel" (p adj channel))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/19 14:20
42	228	(partially fully) near3 depleted near3 MOSFET	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/19 14:22

43	22	(partially and fully) near3 depleted near3 MOSFET	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/19 14:59
44	21	((partially and fully) near3 depleted near3 MOSFET) and (p n)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/19 15:00
45	128	(partially and fully) near3 depleted near3 SOI	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/19 14:59
46	436270	45and bias	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/19 14:59
47	40	((partially and fully) near3 depleted near3 SOI) and bias	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/19 14:59
48	38	(((partially and fully) near3 depleted near3 SOI) and bias) and (p n)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/19 15:00
49	22	48not ((partially and fully) near3 depleted near3 MOSFET)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/19 15:00
50	29	((((partially and fully) near3 depleted near3 SOI) and bias) and (p n)) not ((partially and fully) near3 depleted near3 MOSFET)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/19 15:00